



CT1110-W, CT1111-W, CT1112-W, CT1113-W, CT1114-W CT1115-W, CT1116-W, CT1117-W, CT1118-W, CT1119-W DC Input 5-Pin Long Mini-Flat Phototransistor Optocoupler

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Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- Extra low coupling capacitance
- DC input with transistor output
- Operating Temperature range - 55 °C to 125 °C
- External creepage distance > 8.0 mm
- Clearance distance > 8.4mm
- Distances through insulation > 0.4 mm
- RoHS and REACH Compliance
- Halogen Free Compliance
- MSL class 1
- Regulatory Approvals
 - ✓ UL - UL1577 (E364000)
 - ✓ VDE - EN60747-5-5 (VDE0884-5)
 - ✓ CQC - GB4943.1, GB8898 (19001231775)
 - ✓ IEC62368 (FI/41119)

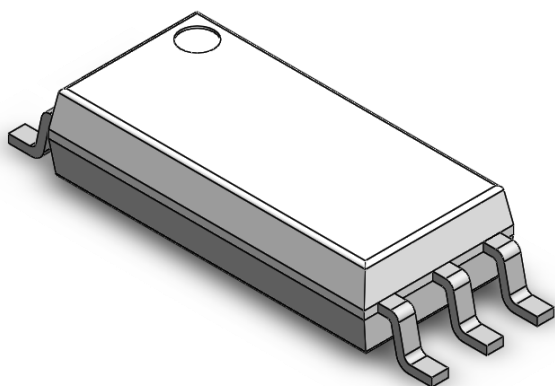
Applications

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

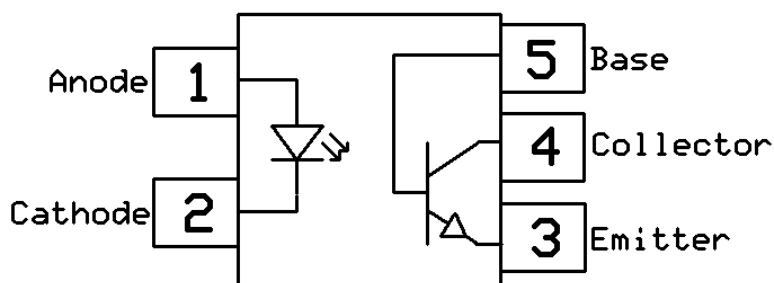
Description

The CT111X-W-H series consists of a photo transistor optically coupled to an Infrared-emitting diode in a 5-lead SOP Package.

Package Outline



Schematic





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Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$, unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
V _{ISO}	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V _{RMS}	
T _{OPR}	Operating temperature	-55 ~ +125	°C	
T _{STG}	Storage temperature	-55 ~ +150	°C	
T _{SOL}	Soldering temperature	260	°C	
Emitter				
I _F	Forward current	50	mA	
I _{F(TRANS)}	Peak transient current (≤1μs P.W, 300pps)	1	A	
V _R	Reverse voltage	6	V	
P _D	Power dissipation	85	mW	
Detector				
P _D	Power dissipation	150	mW	
B _{VCEO}	Collector-Emitter Breakdown Voltage	80	V	
B _{VCBO}	Collector-Base Breakdown Voltage	80	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	7	V	
B _{VEBO}	Emitter-Base Breakdown Voltage	7	V	
I _C	Collector Current	50	mA	



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Electrical Characteristics $T_A = 25^\circ\text{C}$ (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
V_F	Forward voltage	$I_F = 10\text{mA}$	-	1.24	1.4	V	
		$I_F = 50\text{mA}$	-	1.45	1.5	V	
I_R	Reverse Current	$V_R = 6\text{V}$	-	-	5	μA	
C_{IN}	Input Capacitance	$f = 1\text{kHz}$	-	45	-	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{CEO}}$	Collector-Emitter Breakdown	$I_C = 100\mu\text{A}$	80	-	-	V	
$B_{V_{ECO}}$	Emitter-Collector Breakdown	$I_E = 100\mu\text{A}$	7	-	-	V	
$B_{V_{CBO}}$	Collector-Base Breakdown	$I_C = 100\mu\text{A}$	80	-	-	V	
$B_{V_{EBO}}$	Emitter-Base Breakdown	$I_E = 100\mu\text{A}$	7	-	-	V	
I_{CEO}	Collector-Emitter Dark Current	$V_{CE} = 20\text{V}$	-	-	100	nA	
I_{CBO}	Collector-Base Dark Current	$V_{CB} = 20\text{V}$	-	-	20	nA	

Transfer Characteristics

Symbol	Parameters		Test Conditions	Min	Typ	Max	Units	Notes
CTR	Current Transfer Ratio	CT1110-W-H	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$	50	-	600	%	
		CT1115-W-H		50	-	150		
		CT1116-W-H		100	-	300		
		CT1117-W-H		80	-	160		
		CT1118-W-H		130	-	260		
		CT1119-W-H		200	-	400		
		CT1111-W-H	$I_F = 10\text{mA}, V_{CE} = 5\text{V}$	60	-	300		
		CT1112-W-H		63	-	125		
		CT1113-W-H		100	-	200		
		CT1114-W-H		160	-	320		
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage		$I_F = 10\text{mA}, I_C = 1\text{mA}$	-	-	0.4	V	
R_{IO}	Isolation Resistance		$V_{IO} = 500\text{V}_{DC}$	5×10^{10}	-	-	Ω	
C_{IO}	Isolation Capacitance		$f = 1\text{MHz}$	-	-	1	pF	



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Switching Characteristics

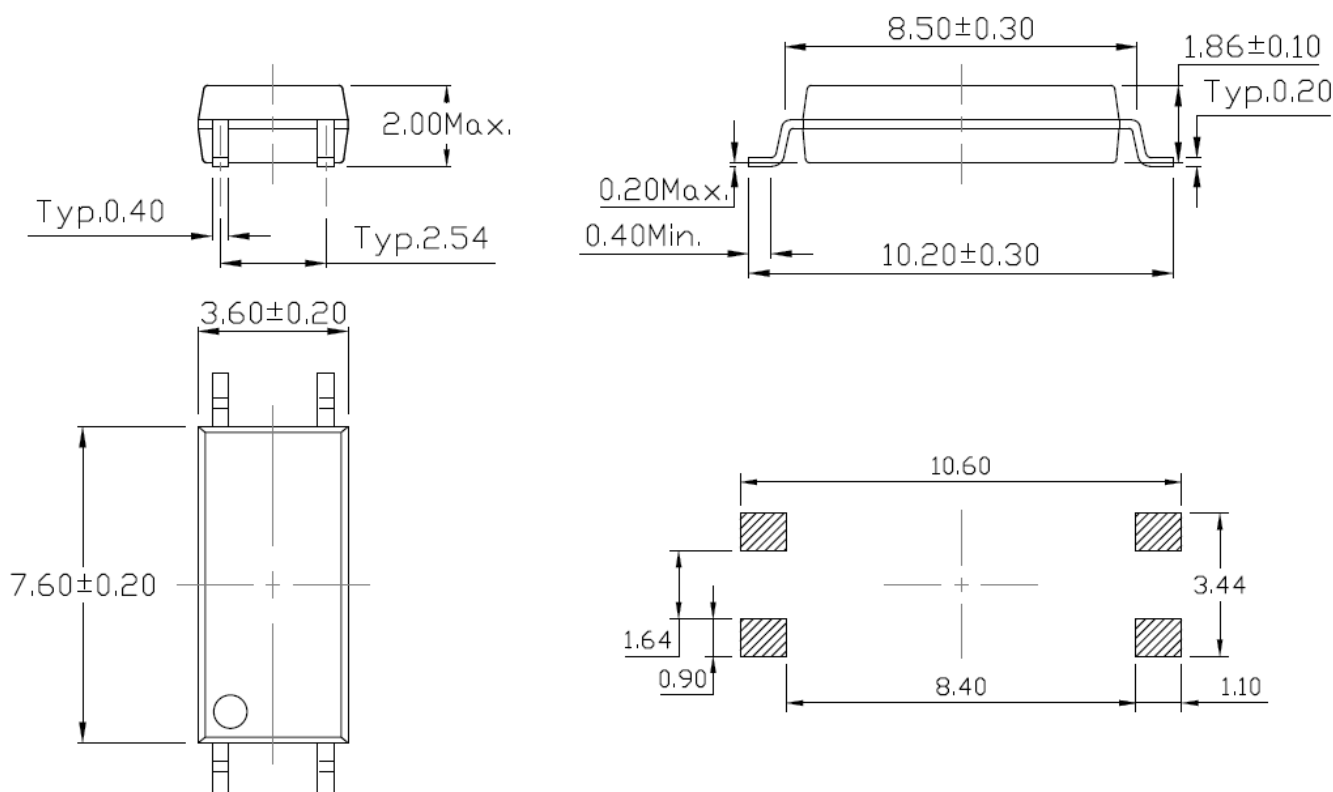
Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
T_{ON}	Turn On Time	$I_C = 5\text{mA}$, $V_{CE} = 5\text{V}$, $R_L = 100\Omega$	-	5	-	μs	
T_{OFF}	Turn Off Time		-	4.2	-		
t_r	Rise Time		-	2.8	-		
t_f	Fall Time		-	4.1	-		



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Package Dimension *Dimensions in mm unless otherwise stated*



Marking Information



Note:

- CT : Denotes "CT Micro"
- 1110 : Part Number
- V : VDE Safety Mark Option (Blank or V)
- Y : One Digit Year Code
- WW : Two Digit Work Week
- K : Manufacturing Code



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Ordering Information

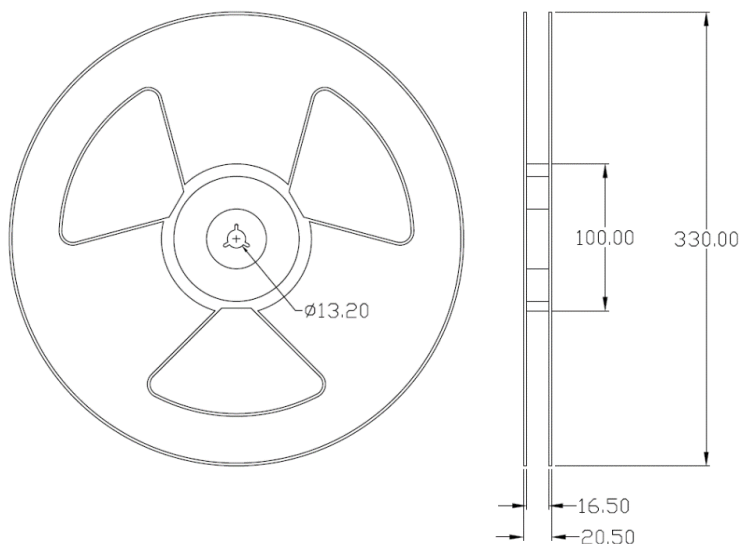
CT111X(V)(Y)-W-H

CT	= Denotes "CT Micro"
111X	= Part Numbers (X= 0,1,2,3,4,5,6,7,8,9)
V	= VDE Safety Mark Option (Blank or V)
Z	= Tape and Reel Option (T1 or T2)
W	= Outline Color (W, White)
H	= Lead frame option (H: Iron, None: Copper)

Option	Description	Quantity
T1	Surface Mount Lead Forming – With Option 1 Taping	3000Units/Reel
T2	Surface Mount Lead Forming – With Option 2 Taping	3000Units/Reel

Reel Dimension *All dimensions are in mm, unless otherwise stated*

Option T1/T2



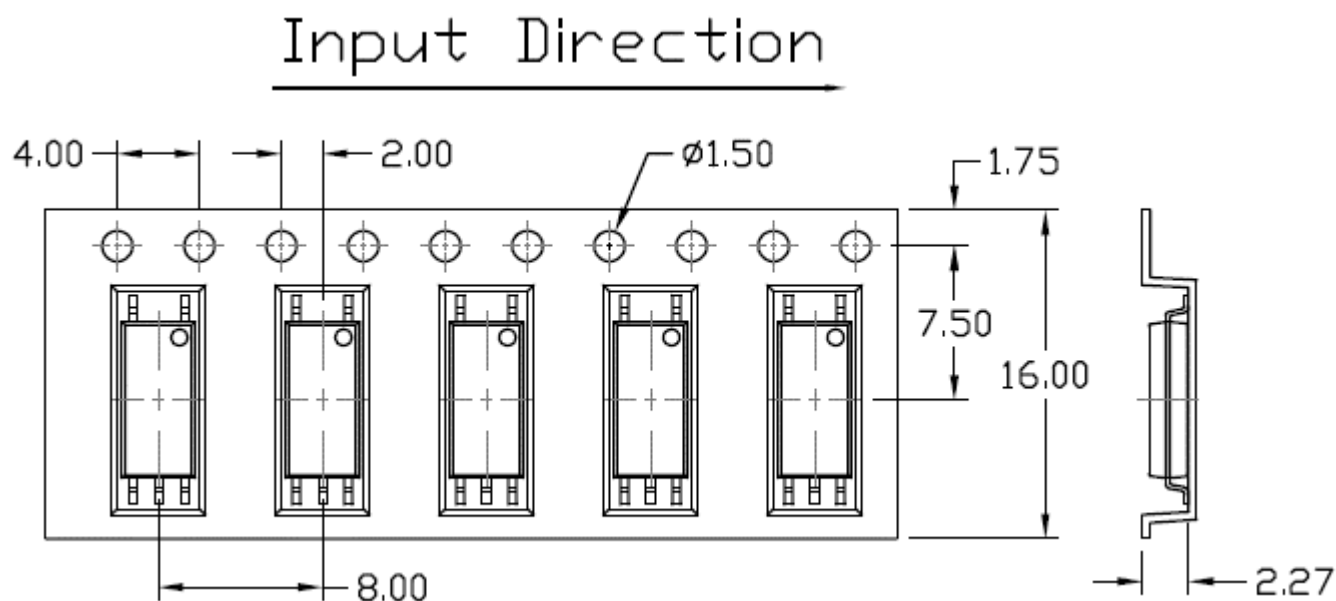


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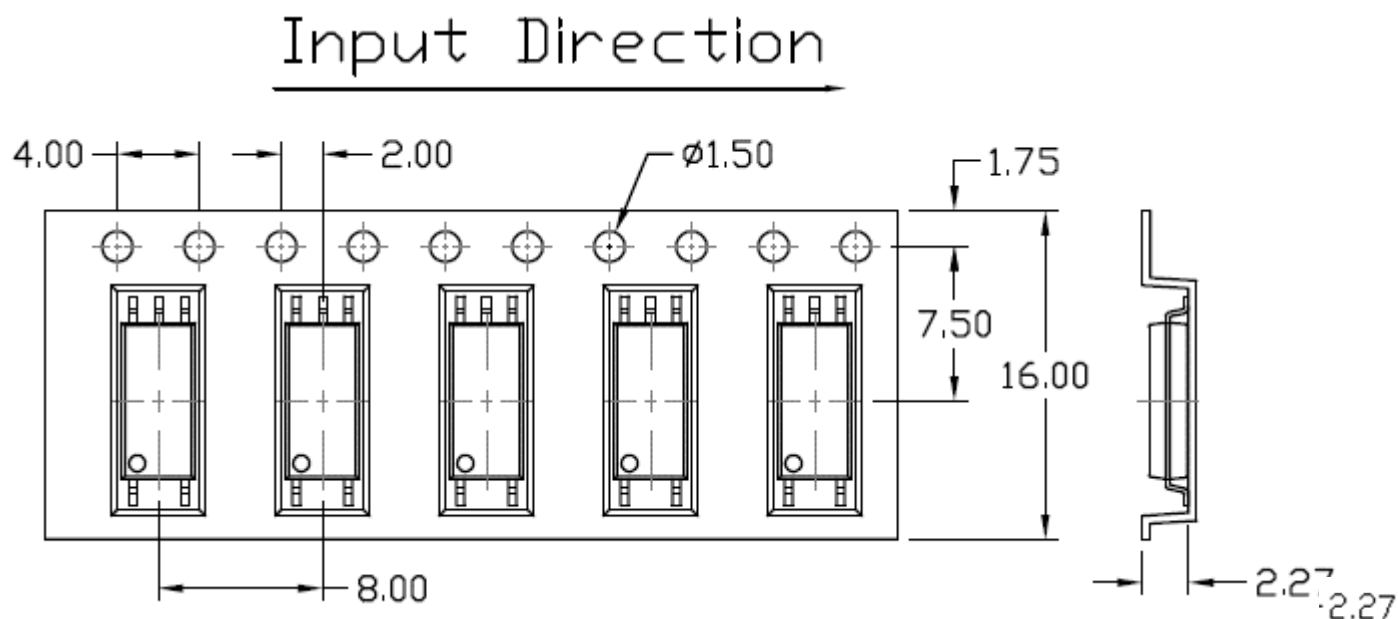
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Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

Option T1



Option T2





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Solderability spec (follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

Wave soldering (follow the JEDEC standard JESD22-A111)

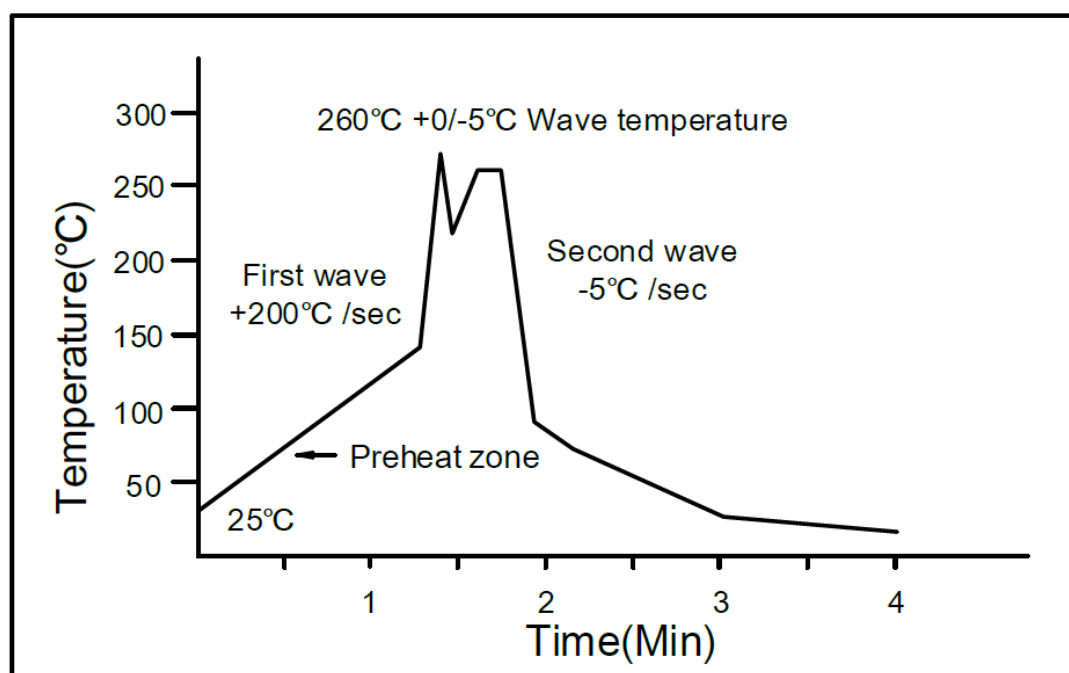
One time soldering is recommended within the condition of temperature.

Temperature: $260 \pm 5^\circ\text{C}$.

Time: 10 sec.

Preheat temperature: 25 to 140°C .

Preheat time: 30 to 80 sec.



Iron soldering (follow the standard MIL-STD 202G, Method 210F)

Allow single lead soldering in every single process.

One time soldering is recommended. Temperature: $350 \pm 10^\circ\text{C}$

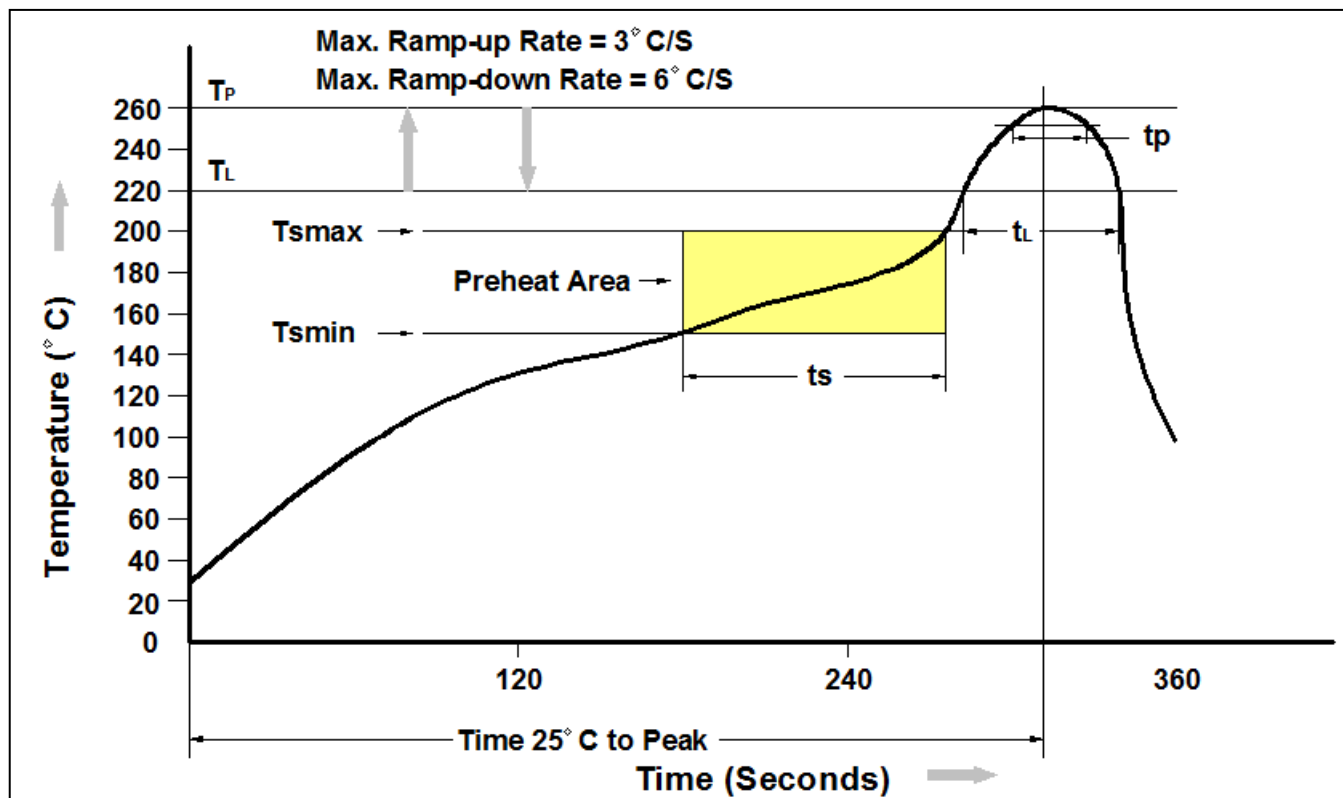
Time: 5 sec max.



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Reflow Profile (follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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